



1.8V 20Gbps DP2.0 Linear ReDriver with AUX Listener & Pin Strap control

Features

- 4-to-4 linear ReDriver™ channel configuration with CTLE gain compensation up to 13.8dB @20Gbps
- Supports 4-lane DP2.0 (UHBR20/UHBR13/UHBR10)/HBR3/ HBR2/HBR/RBR
- Ultra low latency (< 300ps) for better interoperability and data throughput
- 4 level controls on CTLE Gain (7.1 to 13.8dB), Flat Gain (-4 to +2dB)
- Integrated AUX channel listener for D3 power saving mode.
- Low Power DisplayPort active 324mW typical, D3 power down mode 1.8mW typical, Disable Power 27uW typical
- Single Power Supply: 1.8V +/-5%
- Industrial Temperature Support: -40°C to +85°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

- Packaging (Pb-free & Green):
 - Tiny 32-pin, WLGA (FLA) 2.85 x 4.5 mm (0.4 mm pitch, 0.7mm max height)

Description

The DIODES™ PI2DPX2023 is a 20Gbps DP2.0/DP1.4 linear ReDriver in a 4-to-4 configuration operated by a 1.8V power supply. The device supports UHBR20 (DP2.0 20Gbps), UHBR13.5 (DP2.0 13.5Gbps), UHBR10 (DP2.0 10Gbps), HBR3 (DP1.4 8.1Gbps), HBR2 (DP1.2 5.4Gbps), HBR(DP1.1 2.7Gbps) and RBR(DP1.0 1.62Gbps) under various DisplayPort speeds. With the on-chip AUX channel listener, the device can automatically monitor the system operation status to enter D3 power saving mode.

The non-blocking linear redriver design ensures that the differential signals conveying pre-shoot and de-emphasis equalization waveforms from the transmitter side to the receiver side help optimize the overall channel link adjustment conducted by the system transmitter and receiver that has been equipped with DFE. The CTLE equalizers are implemented at the inputs of the redriver to compensate the channel loss and reduce the ISI jitters. The flat gain adjustments support the eye diagram opening. The CTLE EQ gains and flat gains are tuned via pin strap control.

Applications

- Graphics Add In Cards
- Laptop, Desktop and AIO PCs
- Workstation and Servers
- Docking Station
- Display Monitors
- Gaming Console
- Active Cables

Ordering Information

Ordering Number	Package Code	Description		
PI2DPX2023FLAEX	FLA	32-Pin, W-LGA4528-32		

Notes:

1

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel





Revision History

Date	Revision	Description
March 2021	1	Preliminary Datasheet Release
Wiaicii 2021	1	Updated Pin Description & Block Diagram
April 2021	2	Update Pin Description
		Updated Section Description, Feature
		Updated Section Pin Description
October 2021	3	Updated Section CTLE Equalization, Flat Gain, and Chip Enable Control
		Updated Pin Description & Block Diagram Update Pin Description Updated Section Description, Feature Updated Section Pin Description
		Datasheet Release
		Updated Graphics Add In Card Application
I1 2022	4	Updated Section Pin Description
July 2022	4	Updated Section Part Marking
		Updated Section Packaging Mechanical
		Updated Figure 9 Channel Measurement Setup





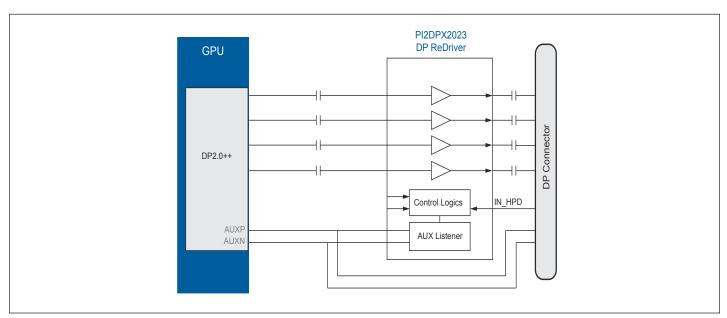
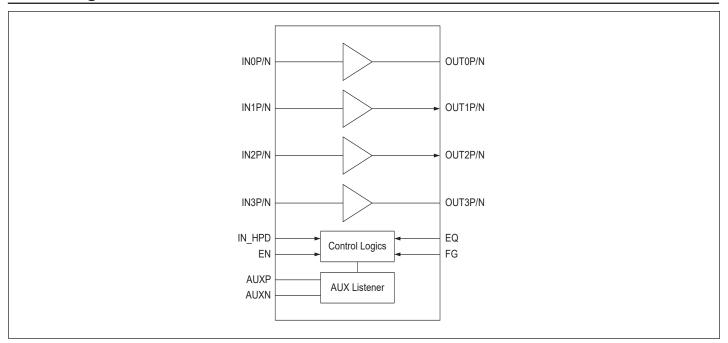


Figure 1. Graphics Add In Card Application





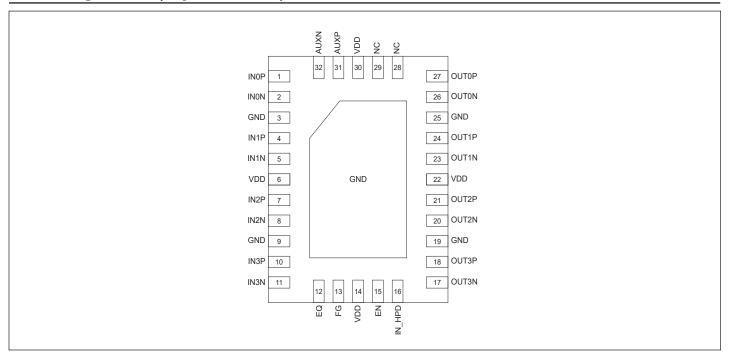
Block Diagram







Pin Configuration (Top-Side View)



Pin Description

Pin#	Pin Name	Type	Description		
Power and GND	ower and GND				
6, 14, 22, 30	6, 14, 22, 30 VDD Power 1.8V power supply, ±5%				
3, 9, 19, 25, Center Pad	GND	Ground	Supply ground		
Control Pins					
12	EQ	Ι	Equalization selection. It is a 4-level input (See Table 3) with internal $100k\Omega$ pull-up resistor and $200k\Omega$ pull-down resistor.		
13	FG	Ι	Flat Gain Selection. It is a 4-level input (See Table 4) with internal $100k\Omega$ pullup resistor and $200k\Omega$ pull-down resistor.		
			Chip Enable. With internal $300 \mathrm{k}\Omega$ pull-up resistor.		
15	EN	I	"Low": Chip Power Down		
			"High": Normal Operation (Default)		
16	IN_HPD	I	Hot Plug Detection from Sink. With internal $300 \mathrm{k}\Omega$ pull-down resistor.		
High Speed I/O Pi	ıs				
18,	OUT3P,				
17	OUT3N		Channel CML output terminals.		
27,	OUT0P,	О	With selectable output termination between 50Ω to VDD or Hi-Z		
26	OUT0N				





Pin Description Cont.

Pin #	Pin Name	Type	Description
21,	OUT2P,		
20	OUT2N	0	Channel CML output terminals.
24,	OUT1P,		With selectable output termination between 50Ω to VDD or Hi-Z
23	OUT1N		
1,	INOP,		
2	IN0N		CML input terminals.
10,	IN3P,	I	With selectable input termination between 50Ω to internal VbiasRx or $78k\Omega$ to internal VbiasRx.
11	IN3N		
4,	IN1P,		
5	IN1N	т.	CML input terminals.
7,	IN2P,	I	With selectable input termination between 50Ω to internal VbiasRx or $78k\Omega$ to internal VbiasRx.
8	IN2N		
Side Band Signal Pins			
29, 28	NC	I/O	No connect. Leave it floating.
31, 32	AUXP, AUXN	I/O	DisplayPort AUX CH differential signal connections





Operation Mode

I/O Termination Resistance under Different Conditions

Symbol	Parameter	Resistance	Units
RX Terminal			
R _{in-pd}	Input res at EN=0	78k to VbiasRx	Ω
R _{in-Active}	Input res at active mode condition	50 to VbiasRx1	Ω
R _{in-DP-standby}	Input res in DP standby mode	78k to VbiasRx	Ω
R _{in-DP-active}	Input res in DP active mode	50 to VbiasRx1	Ω
R _{in-DP-D3}	Input res in DP D3 mode	78k to VbiasRx	Ω
TX Terminal			
R _{out-pd}	Output res at EN=0	78k to VbiasTx	Ω
R _{out-Active}	Output res at active mode condition	50 to VDD	Ω
R _{out-DP-standby}	Output res in DP standby mode	78k to VbiasTx	Ω
R _{out-DP-active}	Output res in DP active mode	50 to VDD	Ω
R _{out-DP-D3}	Output res in DP D3 mode	78k to VbiasTx	Ω

Notes:

- 1) The value of Rin will be updated only after the receiver evaluation. Thus, the value can be 50Ω or $78k\Omega$.
- 2) The value of Rout will be updated only after the receiver evaluation. Thus, the value can be 50Ω or $6k\Omega$.

DisplayPort Mode

By default, all channels will go to active mode if HPD bit = 1. The ON/OFF of each DP channel is controlled by the Aux lane count.

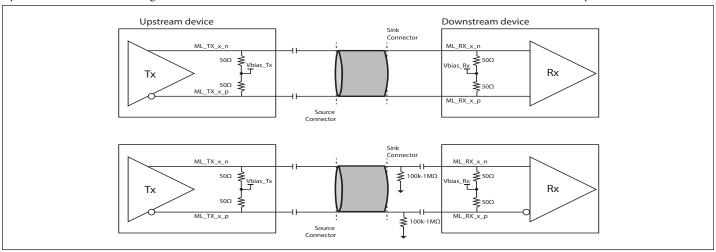


Figure 2. DisplayPort Main Link Connection Diagram





DisplayPort Main Link

The electrical sub-block of a DP Main-Link consists of up to four differential pairs. The DP TX drives doubly terminated, AC-coupled differential pairs in a manner compliant with the Main-Link Transmitter electrical specification.

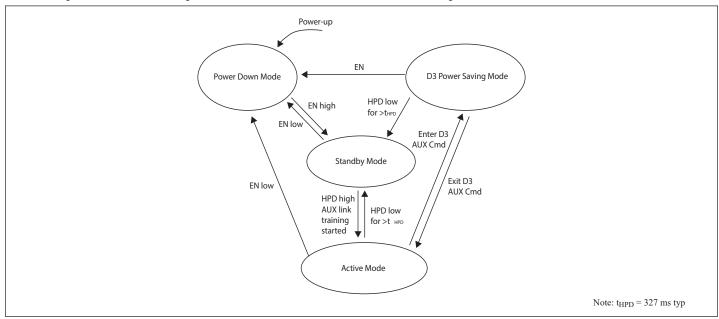


Figure 3. DisplayPort Operation Modes

Table 2. Description of DP Operating Mode

State	Mode	Description
1	Power Down Mode Lowest power consumption (most circuitries are off); all outputs are high-inputs are ignored. AUX listener is turned OFF.	
2	Standby Mode Low power consumption (AUX listener is OFF); Main Link outputs are disabled	
Data transfer (normal operation); Active Mode AUX listener is active. The AUX listener is actively monitor all Main Link outputs are enabled by default. D3 Power Saving Mode Low power consumption(AUX listener is active); Main Link		AUX listener is active. The AUX listener is actively monitoring for Link Training. At power-up
		Low power consumption(AUX listener is active); Main Link outputs are disabled





CTLE Equalization, Flat Gain and Chip Enable Controls

Table 3. CTLE Equalization Gain (Typical Values at FG = 0dB)

EO			Equalizer S	Setting (dB)		
EQ	@1.35GHz	@2.5GHz	@4GHz	@5GHz	@6.7GHz	@10GHz
0	-0.010	0.329	1.070	1.783	3.354	7.126
R	0.104	0.742	1.898	2.931	5.061	9.614
F	F 0.283 1 0.577	1.357	3.012	4.364	6.943	11.858
1		2.256	4.445	6.067	8.923	13.783

Note: R=0.33VDD. F=0.67VDD.

Table 4. Flat Gain Setting (FG)

FG	Flat Gain Setting		
0	-4 dB		
R	-2 dB		
F	+0 dB (Default)		
1	+2 dB		

Note: R=0.33VDD. F=0.67VDD.

Table 5. Chip Enable Control

EN Pin	Channel Operation
0	Disabled
1	Enabled (Default)





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature
Junction Temperature
Supply Voltage to Ground Potential –0.5V to VDD+0.3V
Voltage Input to High Speed Differential Pins0.5V to VDD
Voltage Input to Low Speed Pins (SCL, SDA) $-0.5V$ to $+3.3V$
Voltage Input to Low Speed Pins (AUXP/N) $-0.5V$ to $3.3V$
Voltage Input to Low Speed Pins (EN)0.5V to VDD+0.3V
ESD, HBM
ESD CDM

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Thermal Information

Symbol	Parameter	32-Pin WLGA Package	Units
Theta JA	Junction to Ambient Thermal Resistance	TBD	°C/W

Recommended Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Units
V_{DD}	Supply Voltage	1.71	1.8	1.89	V
V _{DD_Noise}	Power Supply Noise Up to 50MHz	_	_	50	mVpp
V _{RX_CM}	Input Source Common-Mode Noise	_	_	150	mVpp
Cac_coupling	System AC Coupling Capacitance	75	_	265	nF
T_{A}	Ambient Temperature	-40(1)	_	+85	°C

Note:

Power Consumption

Symbol	Parameter	Min.	Тур.	Max.	Units
I _{ON_4DP}	4-lane DP2.0	_	160	220	mA
I_{D3}	DisplayPort D3 power down mode	_	0.9	1.6	mA
I _{ENB}	Disabled mode (EN=Low)	_	8	30	uA
I _{Stdby}	IN_HPD = Low	_	1	1.7	mA

AC/DC Characteristics

 $(VDD = 1.8 \pm 5\%, T_A = -40^{\circ}C \text{ to } 85^{\circ}C)$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V_{DD}	Supply Voltage	_	1.71	1.8	1.89	V

^{1.} The minimum temperature -40°C guaranteed by design





AC/DC Characteristics Cont.

Symbol	Parameter Conditions		Min.	Typ.	Max.	Units
Receiver (RX	K) (100 $Ω$ Differential) Electrical S	pecification	`			
R _{RX-DIFF-DC}	DC Differential Input Impedance		72	_	120	Ω
R _{RX-SINGLE-} DC	DC single ended input impedance to guarantee RxDet	Measured with respect to GND over a voltage of 500mV max	18	_	30	Ω
Z _{RX-HIZ-DC-} PD	DC input CM input impedance for V>0 during reset or power down	(Vcm=0 to 500mV)	25	_	_	kΩ
Cac_coupling	AC coupling capacitance		75	_	265	nF
V _{RX-CM-AC-P}	Rx common mode peak voltage	AC up to 5GHz	_	_	150	mVpeak
V _{RX-CM-DC-} Active-Idle- Delta-P	Common mode peak voltage $\begin{aligned} & \text{Avg}_{\text{U0}} \ (\ V_{\text{TX-D+}} + V_{\text{TX-D-}} \)/2 - \\ & \text{Avg}_{\text{U1}} \ (\ V_{\text{TX-D+}} + V_{\text{TX-D-}} \)/2 \end{aligned}$		_	_	200	mVpeak
Transmitter	(TX) Electrical Specification					
V _{TX-DIFF-PP}	Output differential p-p voltage Swing	Differential Swing V _{TX-D+} - V _{TX-D-}	_	_	1	Vppd
R _{TX-DIFF-DC}	DC Differential TX Impedance		72	_	120	Ω
V _{TX-RCV-DET}	The amount of Voltage change allowed during RxDet	Type-C Tx Spec +/-60mA	_	_	600	mV
Cac-coupling	AC coupling capacitance		75	_	265	nF
R _{TX-DC-CM}	Common mode DC output Impedance		18	_	30	Ω
I _{TX-SHORT}	Transmitter short circuit current limit		_	_	60	mA
V _{TX-C}	Common-Mode Voltage	V _{TX-D+} + V _{TX-D-} /2	VDD-1V	_	VDD	V
V _{TX-DC-CM}	Instantaneous allowed DC common mode voltage at the connector side of the AC coupling capacitors	V _{TX-D+} + V _{TX-D-} /2	0	_	VDD	V
V _{TX-CM-AC-} PP-Active	Active mode TX AC common mode voltage	$V_{TX-D+} + V_{TX-D-}$ for both time and amplitude	_	_	100	mVpp
V _{TX-Idle-Diff-} AC-pp		Between D+ and D- in idle mode. Use the HPF to remove DC components. =1/LPF.	_	_	10	mVppd
V _{TX-Idle-Diff-} DC	Idle mode DC common mode delta voltage $V_{TX-D+} - V_{TX-D-}$	Between D+ and D- in idle mode. Use the LPF to remove AC components. =1/HPF.	_	_	10	mV
Channel Per	formance					
T _{pd}	Latency	From input to output	_	25	150	ps
					1	





AC/DC Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
		EQ = 0		7.1			
	Peaking gain (Compensation	EQ = R		9.6		10	
G_{P}	at 10GHz, relative to 100MHz,	EQ = F	_	11.8	_	dB	
	100mVp-p sine wave input)	EQ= 1		13.7			
		Variation around typical	-2	_	+2	dB	
		FG= 0		-4			
		FG= R		-2		40	
G_{F}	Flat gain (100MHz, EQ<2:0>=000)	FG= F	_	0	_	dB	
		FG= 1		+2			
		Variation around typical	-2	_	+2	dB	
V _{sw_100M}	Output linear swing (at 100MHz)	EQ= 0	_	910	_	mVppd	
V _{sw_10G}	Output linear swing (at 10GHz)	EQ= 0	_	800	_	mVppd	
D _{DNEXT}	Differential near-end crosstalk	100MHz to 10GHz, Fig. 6 ⁽¹⁾	_	-30	-20	dB	
D _{DFEXT} ⁽²⁾	Differential far-end crosstalk	100MHz to 10GHz, Fig. 7 ⁽¹⁾	_	-30	-20	dB	
		100MHz to 10GHz, EQ=0, FG=F, Fig. 7.5	_	0.6	_		
V _{NOISE_IN}	Input-referred noise	100MHz to 10GHz, EQ=1, FG=F, Fig. 8	_	0.3	_	mV _{RMS}	
		100MHz to 10GHz, EQ=0, FG=F, Fig. 8	_	0.3	_		
V _{NOISE_OUT}	Output-referred noise	100MHz to 10GHz, EQ=1, FG=F, Fig. 8	_	0.5	_	mV _{RMS}	
S11 _{DM}	Input differential mode return loss	10MHz to 10GHz differential mode	_	-11.5	-8.1	dB	
S11 _{CM}	Input common mode return loss	1GHz to 10GHz common mode	_	-11.1	-5	dB	
S22 _{DM}	Output differential mode return loss	10MHz to 10GHz differential mode	_	-12.7	-8.1	dB	
S22 _{CM}	Output common mode return loss	1GHz to 10GHz common mode	_	-11.3	-4	dB	
DisplayPort	Electrical Specification						
V _{TX-C}	Common-Mode Voltage	V _{TX-D+} + V _{TX-D-} /2	VDD-1V	_	VDD	V	
V _{TX-AC-CM} HBR_RBR	TX AC common mode voltage for HRB and RBR	Measured using an 8b/10b	_	_	20	mV _{RMS}	
V _{TX-AC-} CM_HBR2	TX AC common mode voltage for HBR2	pattern with 50% transition density	_	_	30	mV _{RMS}	





AC/DC Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{TX-DIFFp-p-} Level0	Differential peak-to-peak output voltage swing Level 0	Tested with Pre-emphasis at	0.34	0.4	0.46	V
V _{TX-DIFFp-p-} Level1	Differential peak-to-peak output voltage swing Level 1	Level 0= 0dB Level 1= 3.5dB	0.51	0.6	0.68	V
V _{TX-DIFFp-p-} Level2	Differential peak-to-peak output voltage swing Level 2	Level 2= 6.0 dB	0.69	0.8	0.92	V
	UHBR20(20Gbps) TP2	_	_	0.45	UI	
	UHBR13(13.5Gbps) TP2		_	_	0.45	UI
	UHBR10(10Gbps) TP2	Measured at Transmit output.	_	_	0.38	UI
Tj TX Total Jitter	HBR3 (8.1Gbps)	Prechannel loss from 2.5dB	_	_	0.27	UI
litter	HBR2 (5.4Gbps)	to 13dB	_	_	0.27	UI
	HBR (2.7Gbps)		_	_	0.294	UI
	RBR (1.62Gbps)		_	_	0.18	UI
AUX Listene	er Electrical Specification					
C _{in}	Input capacitance at , AUXP or AUXN		_	_	10	pF
VT(AUX_lis-tener)	Threshold of the AUX listener	tener VCC = 1.8V		_	220	$_{ m m}V_{ m PPd}$

Note:

Control Pin Specifications

 $(VDD = 1.8 \pm 5\%, T_A = -40^{\circ}C \text{ to } 85^{\circ}C)$

Symbol	Parameter	Min.	Тур.	Max.	Units			
2-level Control Pins								
V_{IH}	DC input logic high	VDD*0.65	_	_	V			
V_{IL}	DC input logic low	_	_	VDD*0.35	V			
I_{IH}	Input high current	_	_	50	uA			
I_{IL}	Input Low current	-50	_	_	uA			
4-level Contro	ol Pins							
V_{IH}	DC input logic "High"	0.92*VDD	VDD	_	V			
V_{IF}	DC input logic "Float"F	0.59*VDD	0.67*VDD	0.75*VDD	V			
V _{IR}	DC input logic "With Rext to GND" R	0.25*VDD	0.33*VDD	0.41*VDD	V			
V_{IL}	DC input logic "Low"	_	GND	0.08*VDD	V			
I_{IH}	Input high current		_	50	uA			

^{1.} Measured using a vector-network analyzer (VNA) with -30dBm power level applied to the adjacent input. The VNA detects the signal at the output of the victim channel. All other inputs and outputs are terminated with 50Ω .

^{2.} Subtract the channel gain from the total gain to derive the actual crosstalk





Control Pin Specifications Cont.

Symbol	Parameter	Min.	Тур.	Max.	Units				
I_{IL}	Input Low current	-75	_	_	uA				
Rext	External resistance connects to GND (+/-5%)	64.6	68	71.4	kΩ				
IN_HPD Inpu	ut Pins								
V_{IH}	DC input logic high	2	_	_	V				
$V_{\rm IL}$	DC input logic low	_	_	0.8	V				
Rin	Termination to GND	100	_		kΩ				

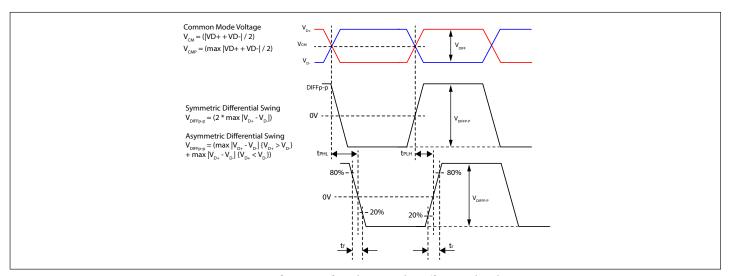


Figure 4. Definition of Peak-to-peak Differential Voltage

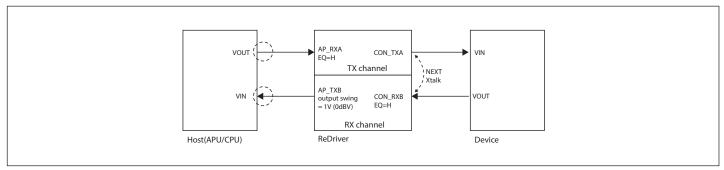


Figure 5. NEXT Crosstalk Definition





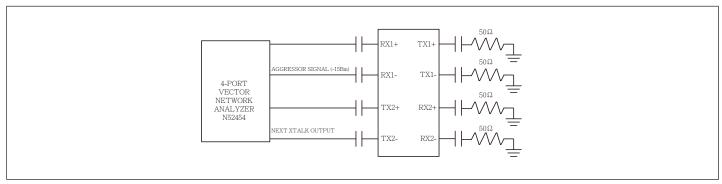


Figure 6. NEXT Channel-isolation Test Configuration

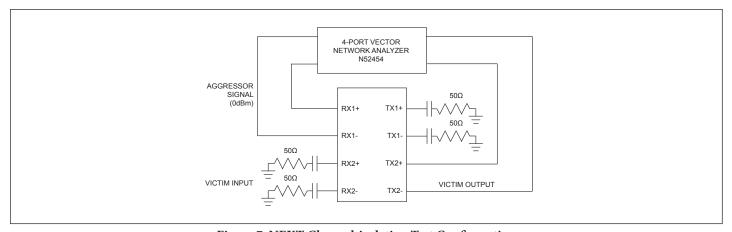


Figure 7. NEXT Channel-isolation Test Configuration

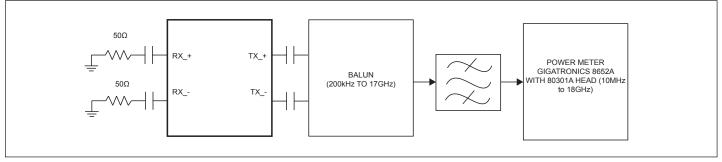


Figure 8. Noise Test Configuration





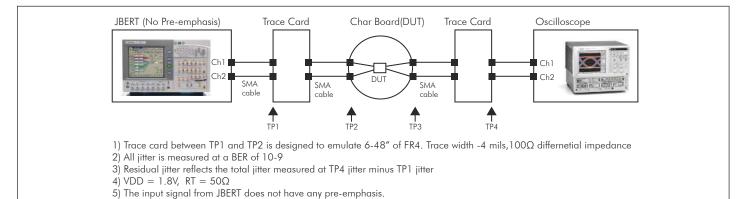


Figure 9. Channel Measurement Setup

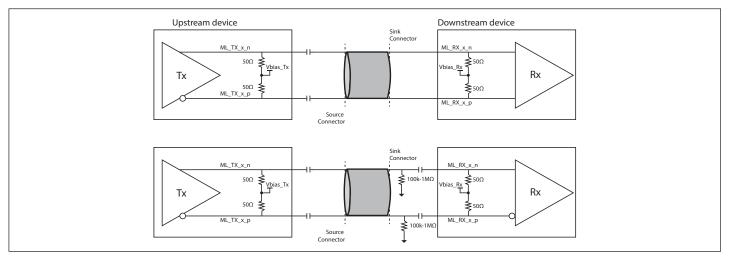


Figure 10. High-speed Channel Test Circuit

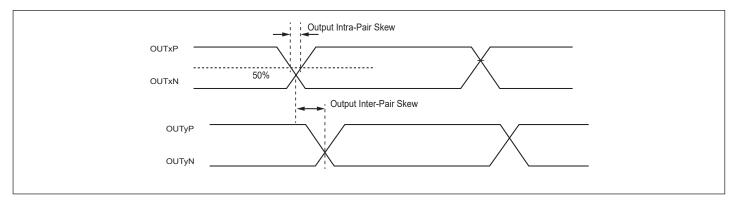
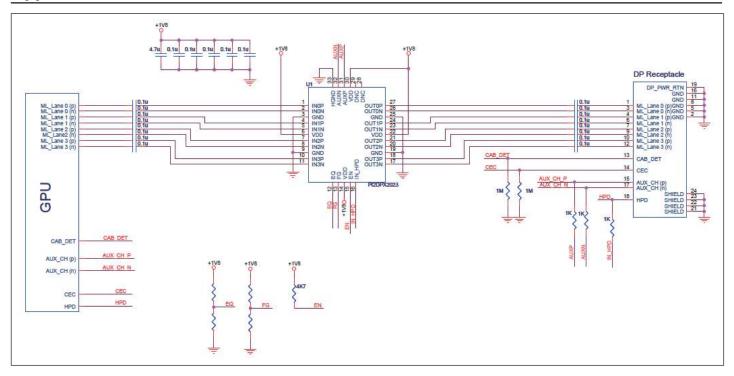


Figure 11. Intra and Inter-pair Differential Skew Definition





Application Schematics

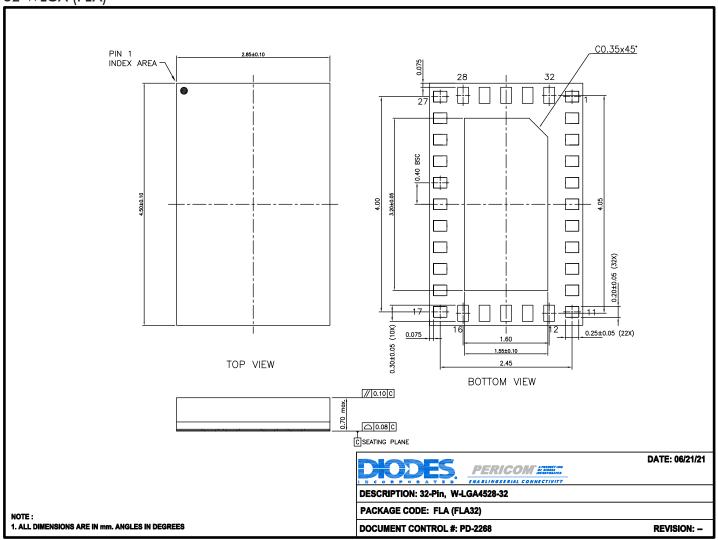






Packaging Mechanical

32-WLGA (FLA)



22-0634

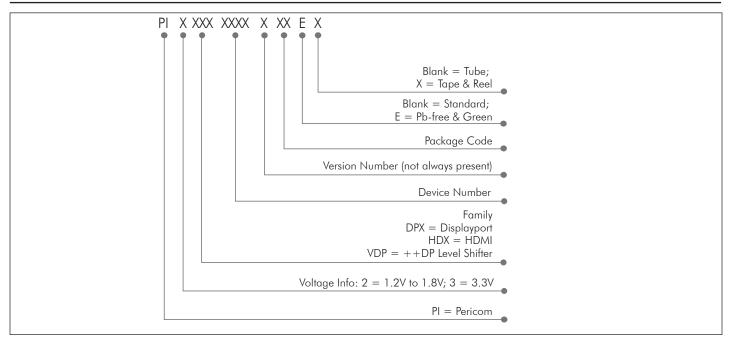
For latest package information:

 $See \ http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.$

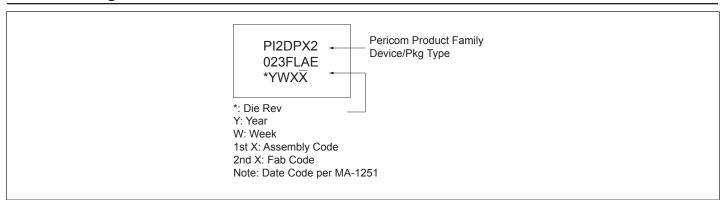




Device Naming Information



Part Marking







Tape & Reel Materials and Design

Carrier Tape

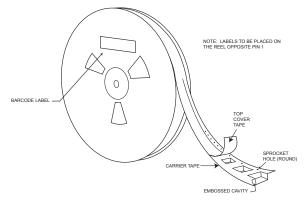
The pocketed carrier tape is made of conductive polystyrene plus carbon material (or equivalent). The surface resistivity is 106Ω /sq. maximum. Pocket tapes are designed so that the component remains in position for automatic handling after cover tape is removed. Each pocket has a hole in the center for automated sensing if the pocket is occupied or not, thus facilitating device removal. Sprocket holes along the edge of the center tape enable direct feeding into automated board assembly equipment. See figures 3 and 4 for carrier tape dimensions.

Cover Tape

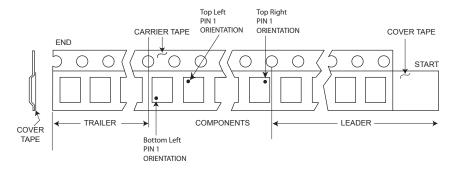
Cover tape is made of anti-static transparent polyester film. The surface resistivity is $107\Omega/\text{sq}$. Minimum to $1011\Omega/\text{sq}$. maximum. The cover tape is heat-sealed to the edges of the carrier tape to encase the devices in the pockets. The force to peel back the cover tape from the carrier tape shall be a MEAN value of 20gm to 80gm (2N to 0.8N).

Reel

The device loading orientation is in compliance with EIA-481, current version (Figure 2). The loaded carrier tape is wound onto either a 13-inch reel (Figure 4) or 7-inch reel. The reel is made of Antistatic High-Impact Polystyrene. The surface resistivity $107\Omega/\text{sq}$, minimum to $1011\Omega/\text{sq}$, maximum.



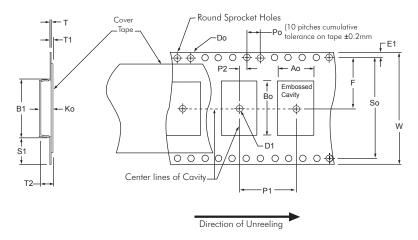
Tape & Reel Label Information



Tape Leader and Trailer Pin 1 Orientations







Standard Embossed Carrier Tape Dimensions

Tape & Reel Dimensions

Constant Dimensions

Constant Di	iiiieiioioiio										
TAPE SIZE	D_0	D ₁ (Min)	E ₁	P ₀	P ₂	R (2)	S ₁ (Min)	T (Max)	T ₁ (Max)		
8mm		1.0			201005	25					
12mm					2.0 ± 0.05		0.6				
16mm	15.0100	1.5	1.75 + 0.1	1.75 + 0.1	1.75 + 0.1	1.75 ± 0.1 4.0 ± 0.1		30	0.6	0.6	
24mm	1.5 +0.1-0.0		1.75 ± 0.1	4.0 ± 0.1	2.0 ± 0.1			0.6	0.1		
32mm		2.0				50	N/A ⁽³⁾				
44mm		2.0			2.0 ± 0.15	50	50 N/A				

Variable Dimensions

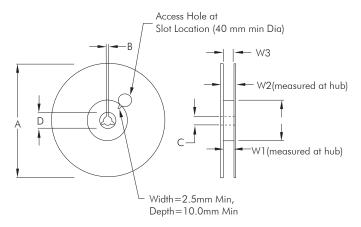
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TAPE SIZE	P_1	B ₁ (Max)	E ₂ (Min)	F	So	T ₂ (Max)	W (Max)	A ₀ , B ₀ &K ₀	
8mm	Specific per package	4.35	6.25	3.5 ± 0.05		2.5	8.3		
12mm	type. Refer to FR-0221 (Tape and Reel Packing	8.2	10.25	5.5 ± 0.05	N/A ⁽⁴⁾	6.5	12.3		
16mm	Information) or visit	10.1	14.25	7.5 ± 0.1	N/A (1)	IN/A	8.0	16.3	C N (1
24mm	www.diodes.com/assets/	20.1	22.25	11.5 ± 0.1		12.0	24.3	See Note 1	
32mm	MediaList-Attachments/ Diodes-Tape-Reel-Tube.	23.0	N/A	14.2 ± 0.1	28.4 ± 0.1	12.0	32.3		
44mm	pdf	35.0	N/A	20.2 ± 0.15	40.4 ± 0.1	16.0	44.3		

NOTES:

- 1. A₀, B₀, and K₀ are determined by component size. The cavity must restrict lateral movement of component to 0.5mm maximum for 8mm and 12mm wide tape and to 1.0mm maximum for 16mm, 24mm, 32mm, and 44mm wide carrier. The maximum component rotation within the cavity must be limited to 200 maximum for 8 and 12 mm carrier tapes and 100 maximum for 16mm through 44mm.
- 2. Tape and components will pass around reel with radius "R" without damage.
- 3. S_1 does not apply to carrier width ≥ 32 mm because carrier has sprocket holes on both sides of carrier where $D_0 \geq S_1$.
- 4. S_0 does not exist for carrier \leq 32mm because carrier does not have sprocket hole on both side of carrier.







Reel Dimensions By Tape Size

TAPE SIZE	A	N (Min) (1)	W_1	W ₂ (Max)	W ₃	B (Min)	С	D (Min)
8mm	178 ± 2.0mm or	60 ± 2.0mm or	8.4 +1.5/-0.0mm	14.4mm				
12mm	330 ± 2.0mm	100 ± 2.0 mm	12.4 +2.0/-0.0mm	18.4mm				
16mm			16.4 +2.0/-0.0mm	22.4mm	Shall Accommodate	1.5	13.0 +0.5/-0.2 mm	20.2
24mm	220 . 2.0	100 : 20	24.4 +2.0/-0.0mm	30.4mm	Tape Width Without Interference	1.5mm	13.0 +0.3/-0.2 11111	20.2mm
32mm	330 ± 2.0mm	100 ± 2.0mm	32.4 +2.0/-0.0mm	38.4mm				
44mm			44.4 +2.0/-0.0mm	50.4mm				

NOTE:

^{1.} If reel diameter A=178 \pm 2.0mm, then the corresponding hub diameter (N(min) will by 60 \pm 2.0mm. If reel diameter A=330 \pm 2.0mm, then the corresponding hub diameter (N(min)) will by 100 \pm 2.0mm.





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